

Vishay Semiconductors

0.5 A Output Current IGBT and MOSFET Driver



DESCRIPTION

The VO3150A consists of a LED optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices. The voltage and current supplied by this optocoupler makes it ideally suited for directly driving IGBTs with ratings up to 800 V/20 A. For IGBTs with higher ratings, the VO3150A can be used to drive a discrete power stage which drives the IGBT gate.

FEATURES

- 0.5 A minimum peak output current
- 25 kV/µs minimum common mode rejection (CMR) at V_{CM} = 1500 V
- I_{CC} = 2.5 mA maximum supply current
- Under voltage lock-out (UVLO) with hysteresis
- Wide operating V_{CC} range: 15 V to 32 V
- 0.4 µs maximum propagation delay
- Industrial temperature range: 40 °C to 110 °C
- 0.5 V maximum low level output voltage (V_{OL})
- Compliant to RoHS directive 2002/95/EC

APPLICATIONS

- Isolated IGBT/MOSFET gate driver
- AC and brushless DC motor drives
- Induction stove top
- Industrial inverters
- Switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

AGENCY APPROVALS

- UL file no. E52744 system code H, double protection
- cUL file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-5 (VDE0884) available with option 1



TRUTH TABLE			
LED	V _{CC} - V _{EE} "POSITIVE GOING" (TURN ON)	V _{CC} - V _{EE} "NEGATIVE GOING" (TURN OFF)	v _o
Off	0 V to 32 V	0 V to 32 V	Low
On	0 V to 11 V	0 V to 9.5 V	Low
On	11 V to 13.5 V	9.5 V to 12 V	Transition
On	13.5 V to 32 V	12 V to 32 V	High



RoHS

COMPLIANT

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ABSOLUTE MAXIMUM RATI	NGS ⁽¹⁾ (T _{amb} = 25 °C, unless ot	herwise specifi	ed)	
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Input forward current		I _F	25	mA
Peak transient input current	< 1 µs pulse width, 300 pps	I _{F(TRAN)}	1	А
Reverse input voltage		V _R	5	V
Output power dissipation		P _{diss}	45	mW
OUTPUT				
High peak output current (2)		I _{OH(PEAK)}	0.5	А
Low peak output current ⁽²⁾		I _{OL(PEAK)}	0.5	А
Supply voltage		(V _{CC} - V _{EE})	0 to + 35	V
Output voltage		V _{O(PEAK)}	0 to + V _{CC}	V
Output power dissipation		P _{diss}	250	mW
OPTOCOUPLER				
Isolation test voltage (between emitter and detector, climate per DIN 500414, part 2, Nov. 74)	t = 1 s	V _{ISO}	5300	V _{RMS}
Storage temperature range		Τ _S	- 55 to + 125	°C
Ambient operating temperature range		T _{amb}	- 40 to + 110	°C
Total power dissipation		P _{tot}	295	mW
Lead solder temperature ⁽³⁾	for 10 s, 1.6 mm below seating plane	T _{sld}	260	°C

Notes

(1) Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Maximum pulse width = 10 μ s, maximum duty cycle = 0.2 %. This value is intended to allow for component tolerances for designs with I_O peak minimum = 0.5 A. See applications section for additional details on limiting I_{OH} peak.

⁽³⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

RECOMMENDED OPERATING CONDITION								
PARAMETER	SYMBOL	MIN.	MAX.	UNIT				
Power supply voltage	V _{CC} - V _{EE}	15	32	V				
Input LED current (on)	١ _F	7	16	mA				
Input voltage (off)	V _{F(OFF)}	- 3	0.8	V				
Operating temperature	T _{amb}	- 40	+ 110	°C				



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THERMAL CHARACTERISTICS			
PARAMETER	SYMBOL	VALUE	UNIT
LED power dissipation	P_{diss}	45	mW
Output power dissipation	P _{diss}	250	mW
Total power dissipation	P _{tot}	285	mW
Maximum LED junction temperature	T _{jmax.}	125	°C
Maximum output die junction temperature	T _{jmax.}	125	°C
Thermal resistance, junction emitter to board	θ_{JEB}	169	°C/W
Thermal resistance, junction emitter to case	θ_{JEC}	192	°C/W
Thermal resistance, junction detector to board	θ_{JDB}	82	°C/W
Thermal resistance, junction detector to case	θ_{JDC}	80	°C/W
Thermal resistance, junction emitter to junction detector	θ_{JED}	200	°C/W
Thermal resistance, case to ambient	θ_{CA}	2645	°C/W

Note

 The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's Thermal Characteristics of Optocouplers application note.

ELECTRICAL CHARACTE						-
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
High level output current	$ I_{F} = 16 \text{ mA}, R_{g} = 10 \ \Omega, C_{g} = 20 \text{ nF}, \\ V_{CC} = 15 \text{ V}, V_{EE} = 0 \text{ V} $	I _{OH} ⁽³⁾	0.5			А
Low level output current	$ I_F = 0 \text{ mA}, \text{R}_g = 10 \ \Omega, \text{C}_g = 20 \text{ nF}, \\ \text{V}_{\text{CC}} = 15 \text{ V}, \text{V}_{\text{EE}} = 0 \text{ V} $	I _{OL} ⁽³⁾	0.5			А
High level output voltage	I _O = - 100 mA	V _{OH} ⁽⁴⁾	V _{CC} - 4	V _{CC} - 2.1		V
Low level output voltage	I _O = 100 mA	V _{OL}		0.2	0.5	V
High level supply current	Output open, $I_F = 7$ mA to 16 mA	I _{CCH}			2.5	mA
Low level supply current	Output open, $V_F = -3 V \text{ to } + 0.8 V$	I _{CCL}			2.5	mA
Threshold input current low to high	I _O = 0 mA, V _O > 5 V	I _{FLH}		2.1	5	mA
Threshold input voltage high to low		V _{FHL}	0.8			V
Input forward voltage	I _F = 10 mA	V _F	1	1.3	1.6	V
Temperature coefficient of forward voltage	I _F = 10 mA	$\Delta V_{F} / \Delta T_{A}$		- 1.4		mV/°C
Input reverse breakdown voltage	I _R = 10 μA	BVP	5			V
Input capacitance	f = 1 MHz, V _F = 0 V	C _{IN}		60		pF
IN/I O thread and	$V_O \ge 5 V$	V _{UVLO+}	11	12.6	13.5	V
UVLO threshold	I _F = 10 mA	V _{UVLO-}	9.5	10.7	12	V
UVLO hysteresis		UVLO _{HYS}		1.9		V

Notes

⁽¹⁾ Minimum and maximum values were tested over recommended operating conditions ($T_{amb} = -40$ °C to 110 °C, $I_{F(ON)} = 7$ mA to 16 mA, $V_{F(OFF)} = -3$ V to 0.8 V, $V_{CC} = 15$ V to 32 V, $V_{EE} =$ ground) unless otherwise specified. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements. All typical values were measured at $T_{amb} = 25$ °C and with $V_{CC} - V_{EE} = 32$ V.

⁽²⁾ Maximum pulse width = 50 μ s, maximum duty cycle = 0.5 %.

⁽³⁾ Maximum pulse width = 10 μ s, maximum duty cycle = 0.2 %. This value is intended to allow for component tolerances for designs with I_O peak minimum = 0.5 A.

⁽⁴⁾ In this test V_{OH} is measured with a dc load current. When driving capacitive loads V_{OH} will approach V_{CC} as I_{OH} approaches zero A. Maximum pulse width = 1 ms, maximum duty cycle = 20 %.

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TEST CIRCUITS



Fig. 1 - I_{OH} Test Circuit



Fig. 2 - I_{OL} Test Circuit



Fig. 3 - V_{OH} Test Circuit







Fig. 5 - I_{FLH} Test Circuit



Fig. 6 - UVLO Test Circuit

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Propagation delay time to logic low output ⁽¹⁾	$\label{eq:Rg} \begin{array}{l} R_g = 47 \; \Omega, C_g = 3 \; nF, f = 10 \; kHz, \\ duty \; cycle = 50 \; \% \end{array}$	t _{PHL}	0.1		0.4	μs	
Propagation delay time to logic high output ⁽¹⁾	$\label{eq:Rg} \begin{array}{l} R_{g} = 47 \; \Omega, C_{g} = 3 \; nF, f = 10 \; kHz, \\ duty \; cycle = 50 \; \% \end{array}$	t _{PLH}	0.1		0.4	μs	
Pulse width distortion ⁽²⁾	$\label{eq:Rg} \begin{array}{l} R_{g} = 47 \; \Omega, C_{g} = 3 \; nF, f = 10 \; kHz, \\ duty \; cycle = 50 \; \% \end{array}$	PWD			0.2	μs	
Propagation delay difference between any two parts ⁽³⁾	$\label{eq:Rg} \begin{array}{l} R_g = 47 \; \Omega, C_g = 3 \; nF, f = 10 \; kHz, \\ duty \; cycle = 50 \; \% \end{array}$	PDD (t _{PHL} - t _{PLH})	- 0.35		0.35	μs	
Rise time	$\label{eq:Rg} \begin{array}{l} R_{g} = 47 \; \Omega, C_{g} = 3 \; nF, f = 10 \; kHz, \\ duty \; cycle = 50 \; \% \end{array}$	t _r		0.1		μs	
Fall time	$\label{eq:Rg} \begin{array}{l} R_{g} = 47 \; \Omega, C_{g} = 3 \; nF, f = 10 \; kHz, \\ \qquad $	t _f		0.1		μs	



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SWITCHING CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
UVLO turn on delay	$V_{O} > 5 V, I_{F} = 10 mA$	T _{UVLO-ON}		0.8		μs		
UVLO turn off delay	$V_{O} > 5 V$, $I_{F} = 10 mA$	T _{UVLO-OFF}		0.6		μs		

Notes

 $^{(1)}\,$ This load condition approximates the gate load of a 1200 V/25 A IGBT.

 $^{(2)}\,$ Pulse width distortion (PWD) is defined as $|t_{PHL}$ - $t_{PLH}|$ for any given device.

⁽³⁾ The difference between t_{PHL} and t_{PLH} between any two VO3150A parts under the same test condition.



Fig. 7 - t_{PLH} , t_{PHL} , t_r and t_f Test Circuit and Waveforms

COMMON MODE TRANSIENT IMMUNITY								
PARAMETER TEST CONDITION SYMBOL MIN. TYP. MAX. UNIT								
Common mode transient immunity at logic high output ⁽¹⁾⁽²⁾	$T_A = 25 \text{ °C}, I_F = 10 \text{ mA to } 16 \text{ mA}, V_{CM} = 1500 \text{ V}, V_{CC} = 32 \text{ V}$	CM _H	25	35		kV/μs		
Common mode transient immunity at logic low output ⁽¹⁾⁽³⁾	$T_A = 25 \ ^{\circ}C, V_{CM} = 1500 \ V, V_{CC} = 32 \ V, V_F = 0 \ V$	CM _L	25	35		kV/µs		

Notes

 $^{(1)}\,$ Pins 1 and 4 need to be connected to LED common.

⁽²⁾ Common mode transient immunity in the high state is the maximum tolerable $|dV_{CM}/dt|$ of the common mode pulse, V_{CM} , to assure that the output will remain in the high state (i.e., $V_O > 15$ V).

⁽³⁾ Common mode transient immunity in a low state is the maximum tolerable $|dV_{CM}/dt|$ of the common mode pulse, V_{CM} , to assure that the output will remain in a low state (i.e., $V_O < 1$ V).





V_{CM}

Dt

V_{OH}

VOL

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SAFETY AND INSULATION RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Climatic classification (according to IEC 68 part 1)				40/110/21				
Comparative tracking index		CTI	175		399			
V _{IOTM}			8000			V		
V _{IORM}			890			V		
P _{SO}					500	mW		
I _{SI}					300	mA		
T _{SI}					175	°C		
Creepage distance	Standard DIP-8		7			mm		
Clearance distance	Standard DIP-8		7			mm		
Creepage distance	400 mil DIP-8		8			mm		
Clearance distance	400 mil DIP-8		8			mm		

Note

• As per IEC 60747-5-5, §7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of prodective circuits.

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)



Fig. 9 - High Output Voltage Drop vs. Temperature



Fig. 10 - High Output Current vs. Temperature







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Fig. 13 - Output Low Voltage vs. Output Low Current



Fig. 14 - Output High Voltage Dropvs. Output High Current



Fig. 15 - Supply Current vs. Temperature



Fig. 16 - Supply Current vs. Supply Voltage



Fig. 17 - Low to High Current Threshold vs. Temperature



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Fig. 19 - Propagation Delay vs. Supply Voltage



Fig. 20 - Propagation Delay vs. Temperature



Fig. 21 - Propagation Delay vs. Forward LED Current



Fig. 22 - Propagation Delay vs. Series Load Resistance



Fig. 23 - Propagation Delay vs. Series Load Capacitance



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PACKAGE DIMENSIONS in millimeters







i178006

Option 7



PACKAGE MARKING



Note

• VDE logo is only marked on option 1 parts. Option information is not marked on the part.



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